

### N-channel 60 V 14.8 mΩ standard level MOSFET

Rev. 3 — 23 June 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### **1.2 Features and benefits**

- High efficiency due to low switching and conduction losses
- 1.3 Applications
  - DC-to-DC converters
  - Load switching

- Suitable for standard level gate drive sources
- Motor control
- Server power supplies

### **1.4 Quick reference data**

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	60	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see Figure 1	-	-	50	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	86	W
Tj	junction temperature		-55	-	175	°C
Static ch	aracteristics					
$R_{DSon}$	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \\ T_{j} = 100 \ ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12} \end{array}$	-	-	23.7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	12.6	14.8	mΩ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$	-	4.7	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	20.9	-	nC
Avalanc	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \\ I_{D} = 50 \text{ A}; \ V_{sup} \leq 60 \text{ V}; \\ R_{GS} = 50 \ \Omega; \ unclamped \end{array} $	-	-	44	mJ

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

### 3. Ordering information

### Table 3.Ordering information

Type number	Package			
	Name	Description	Version	
PSMN015-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78	

SOT78 (TO-220AB)

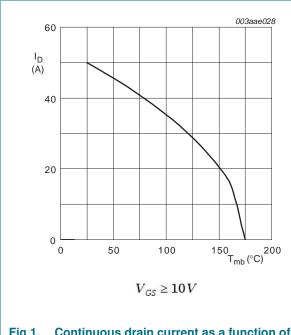
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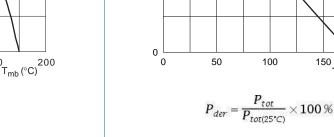
### 4. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	36	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	50	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	201	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	86	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	50	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	201	А
Avalanche rug	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V};  \text{T}_{j(init)} = 25 \text{ °C};  \text{I}_{D} = 50 \text{ A}; \\ V_{sup} \leq 60 \text{ V};  \text{R}_{GS} = 50  \Omega; \text{ unclamped} \end{array} $	-	44	mJ



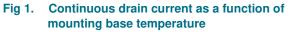


120

80

40

P<sub>der</sub> (%)



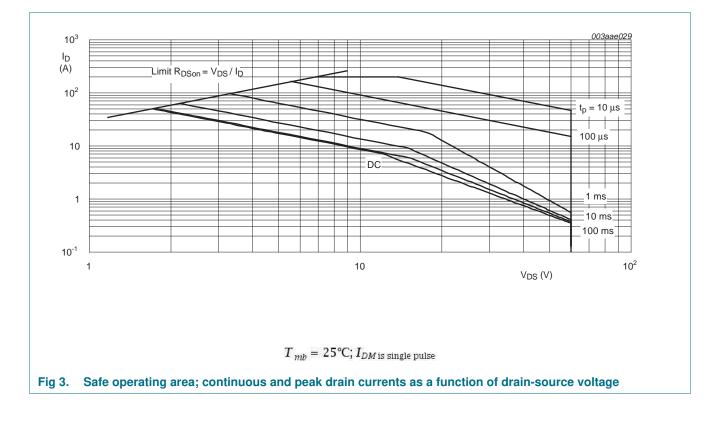


03aa16

150 200 T<sub>mb</sub> (°C)

# **PSMN015-60PS**

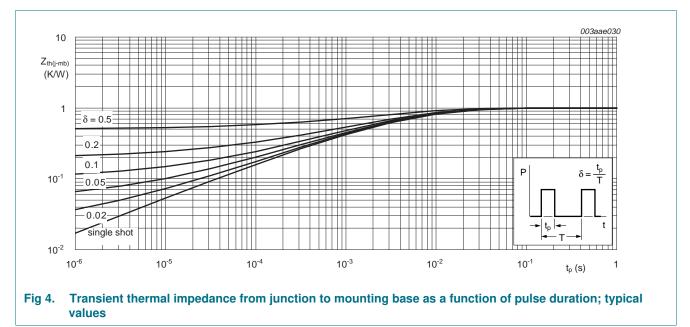
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### 5. Thermal characteristics

Parameter thermal resistance from junction to mounting	Conditions see Figure 4	Min	Тур	Max	Unit
thermal resistance from junction to mounting	see Figure 4				
base	see <u>rigure 4</u>	-	1	1.74	K/W
thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



### Table 5. Thermal characteristics

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### 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	54	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 11</u>	-	-	4.8	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 11</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	0.03	2	μA
		$V_{DS} = 60 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 125 ^{\circ}\text{C}$	-	-	30	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; \text{ V}_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	10	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	28.9	34	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	23.7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	12.6	14.8	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.3	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 30 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	20.9	-	nC
		$I_D = 0 \text{ A};  V_{DS} = 0  \text{V};  V_{GS} = 10  \text{V}$	-	17	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 25 A; $V_{DS}$ = 30 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	6.2	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 25 \text{ A}; \text{ V}_{DS} = 30 \text{ V}; \text{ V}_{GS} = 10 \text{ V};$ see Figure 14	-	3.7	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	2.4	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.7	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 30 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.8	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	1220	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	169	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	95	-	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	12	-	ns
r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	13	-	ns
d(off)	turn-off delay time		-	27	-	ns
t <sub>f</sub>	fall time		-	7	-	ns

Table 6.

Symbol

Source-drain diode

Characteristics ... continued

Parameter

# **PSMN015-60PS**

Max

Тур

Unit

### N-channel 60 V 14.8 mΩ standard level MOSFET

Min

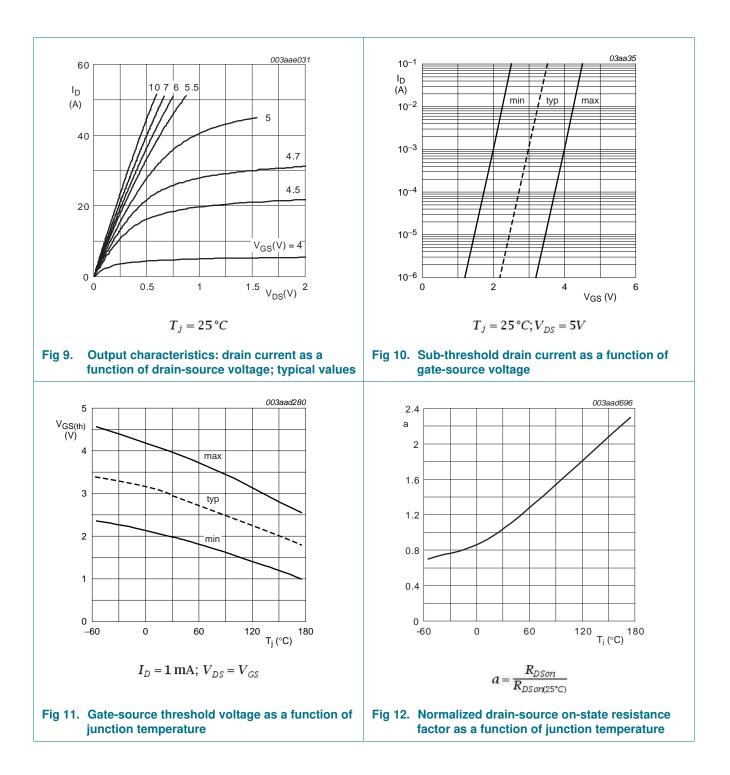
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#### I<sub>S</sub> = 15 A; V<sub>GS</sub> = 0 V; T<sub>i</sub> = 25 °C ٧ source-drain voltage 0.8 $V_{SD}$ 1.2 $I_{\rm S} = 25 \text{ A}; \text{ dI}_{\rm S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ reverse recovery time 31 ns t<sub>rr</sub> -- $V_{GS} = 0 V; V_{DS} = 30 V$ $Q_r$ recovered charge 28.5 nC --003aae032 003aae033 50 50 g<sub>fs</sub> $I_D$ (S) (A) 40 40 30 30 20 20 10 10 T<sub>j</sub> = 175 °C T<sub>i</sub> = 25 °C 0 0 I<sub>D</sub>(A) 50 0 10 20 30 40 0 2 4 6 $V_{GS}(V)$ $T_j = 25 \,^{\circ}C; V_{DS} = 10 \, V$ $V_{DS} > I_D \times R_{DSon}$ Forward transconductance as a function of Transfer characteristics: drain current as a Fig 5. Fig 6. drain current; typical values function of gate-source voltage; typical values 003aae035 003aae036 2000 50 R<sub>DSon</sub> С $(m\Omega)$ (pF) C<sub>iss</sub> 40 1500 30 Crss 1000 20 500 10 0 0 8 10 V<sub>GS</sub>(V) 15 <sub>VGS</sub>(V)<sup>20</sup> 2 4 6 5 10 0 0 $V_{DS} = 0V; f = 1MHz$ $T_j = 25 \,^{\circ}C; I_D = 10A$ Fig 7. Input and reverse transfer capacitances as a Fig 8. Drain-source on-state resistance as a function function of gate-source voltage; typical values of gate-source voltage; typical values

Conditions

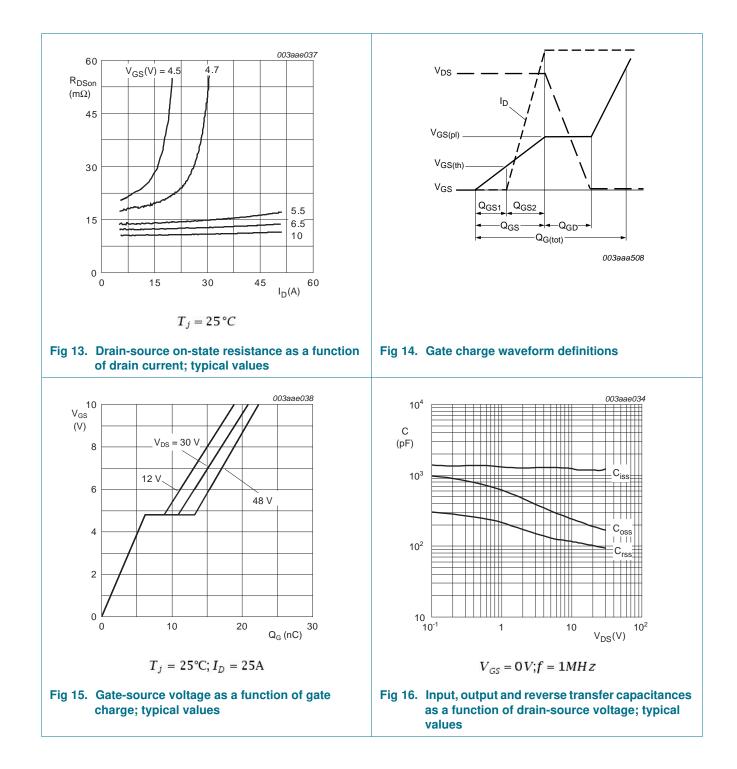
# **PSMN015-60PS**

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### 7. Package outline

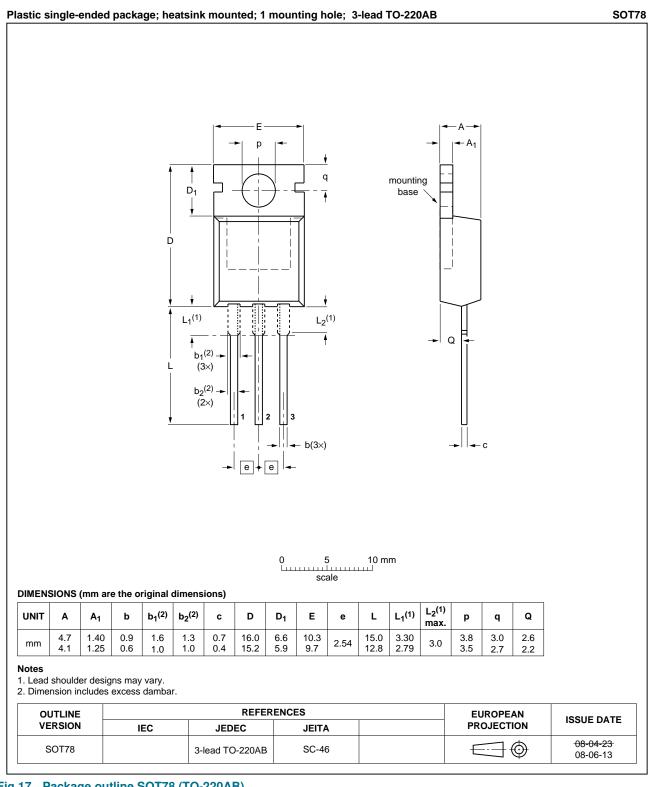


Fig 17. Package outline SOT78 (TO-220AB)

PSMN015-60PS Product data sheet

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### 8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN015-60PS v.3	20110623	Product data sheet	-	PSMN015-60PS v.2
Modifications:	<ul> <li>Status change</li> </ul>	d from objective to product.		
	<ul> <li>Various chang</li> </ul>	es to content.		
PSMN015-60PS v.2	20100222	Objective data sheet	-	PSMN015-60PS v.1

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### 9. Legal information

### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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